

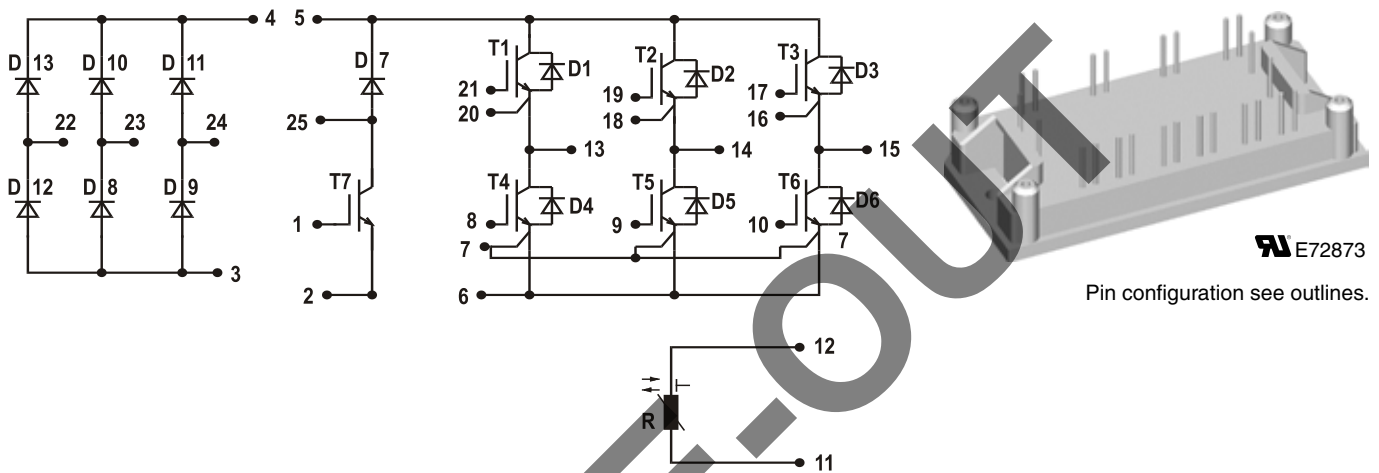
Converter - Brake - Inverter Module (CBI 1) NPT IGBT

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{DAVM25} = 90 \text{ A}$	$I_{C25} = 12 \text{ A}$	$I_{C25} = 52 \text{ A}$
$I_{FSM} = 300 \text{ A}$	$V_{CE(sat)} = 2.5 \text{ V}$	$V_{CE(sat)} = 2.5 \text{ V}$

Preliminary data

Part name (Marking on product)

MUBW10-06A6K



E72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
- low saturation voltage
- positive temperature coefficient
- fast switching
- short tail current
- Epitaxial free wheeling diodes with hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Application:

- AC motor drives with
- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- Electric braking operation

Package:

- UL registered
- Industry standard E1-pack

Output Inverter T1 - T6

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$			600	V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			11	A	
I_{C80}		$T_C = 80^{\circ}\text{C}$			8	A	
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			50	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}; V_{GE} = 15\text{ V}$			2.7 3.1	V V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.2\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5		6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.0	65 mA	
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$				120	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			220		pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 6\text{ A}$			32		nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 6\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 54\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$		20		ns
t_r	current rise time				10		ns
$t_{d(off)}$	turn-off delay time				110		ns
t_f	current fall time				30		ns
E_{on}	turn-on energy per pulse				0.22		mJ
E_{off}	turn-off energy per pulse				0.26		mJ
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 54\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$		18		A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 54\ \Omega;$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$		10		μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			2.75		K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)			0.95		K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			600	V	
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			21	A	
I_{F80}		$T_C = 80^{\circ}\text{C}$			14	A	
V_F	forward voltage	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.2 1.6	V V	
I_{RM}	max. reverse recovery current	$V_R = 100\text{ V}$ $di_f/dt = -100\text{ A}/\mu\text{s}$ $I_F = 12\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 100^{\circ}\text{C}$		80		A
t_{rr}	reverse recovery time				tdb		ns
$E_{rec(off)}$	reverse recovery energy						μJ
R_{thJC}	thermal resistance junction to case	(per diode)			2.5		K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)			0.85		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake Chopper T7

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{CES}	collector emitter voltage		$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			V
V_{GES}	max. DC gate voltage	continuous			± 20	V
V_{GEM}	max. transient collector gate voltage	transient			± 30	V
I_{C25}	collector current		$T_C = 25^{\circ}\text{C}$			A
I_{C80}			$T_C = 80^{\circ}\text{C}$			A
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}; V_{GE} = 15\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.65 3.1	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.2\text{ mA}; V_{GE} = V_{CE}$	4.5	$T_{VJ} = 25^{\circ}\text{C}$		6.5 V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.7 mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$				120 nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			220	pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 6\text{ A}$			32	nC
$t_{d(on)}$	turn-on delay time	} inductive load $V_{CE} = 300\text{ V}; I_C = 6\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 54\ \Omega$		$T_{VJ} = 125^{\circ}\text{C}$	20	ns
t_r	current rise time		10		ns	
$t_{d(off)}$	turn-off delay time		110		ns	
t_f	current fall time		30		ns	
E_{on}	turn-on energy per pulse		0.21		mJ	
E_{off}	turn-off energy per pulse		0.26		mJ	
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 54\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$		$T_{VJ} = 125^{\circ}\text{C}$	18	A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 54\ \Omega;$ non-repetitive		$T_{VJ} = 125^{\circ}\text{C}$	10	μs
R_{thJC}	thermal resistance junction to case	(per IGBT)				2.75 K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)			0.9	K/W

Brake Chopper D7

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 150^{\circ}\text{C}$			V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			A
I_{F80}			$T_C = 80^{\circ}\text{C}$			A
V_F	forward voltage	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.25	2.1 V V
I_R	reverse current	$V_R = V_{RRM}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.2	0.06 mA mA
I_{RM}	max. reverse recovery current	} $V_R = 100\text{ V}; I_F = 12\text{ A}$ $di_F/dt = -100\text{ A}/\mu\text{s}$		$T_{VJ} = 100^{\circ}\text{C}$	3.5	A
t_{rr}	reverse recovery time		80		ns	
R_{thJC}	thermal resistance junction to case	(per diode)				2.5 K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)			0.85	K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Input Rectifier Bridge D8 - D13

Symbol	Definitions	Conditions	Maximum Ratings	
V_{RRM}	max. repetitive reverse voltage		1600	V
I_{FAV}	average forward current	sine 180°	$T_C = 80^\circ\text{C}$	22 A
I_{DAVM}	max. average DC output current	rectangular; $d = 1/3$; bridge	$T_C = 80^\circ\text{C}$	61 A
I_{FSM}	max. surge forward current	$t = 10\text{ ms}$; sine 50 Hz	$T_C = 25^\circ\text{C}$	300 A
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$	50 W

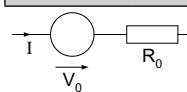
Symbol	Conditions	Characteristic Values			Unit	
		min.	typ.	max.		
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^\circ\text{C}$	1.1	1.45	V
			$T_{VJ} = 125^\circ\text{C}$	1.2		V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$	0.3	0.01	mA
			$T_{VJ} = 125^\circ\text{C}$			mA
R_{thJC}	thermal resistance junction to case	(per diode)	$T_{VJ} = 25^\circ\text{C}$		2.1	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.7		K/W

Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
R_{25}	resistance		$T_C = 25^\circ\text{C}$	4.45	4.7	5.0	k Ω
$B_{25/85}$					3510		K

Module

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		150	$^\circ\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^\circ\text{C}$
T_{stg}	storage temperature		-40		125	$^\circ\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz			2500	V~
M_d	mounting torque	(M4)	2.0		2.2	Nm
d_S	creep distance on surface		12.7			mm
d_A	strike distance through air		9.6			mm
Weight				40		g

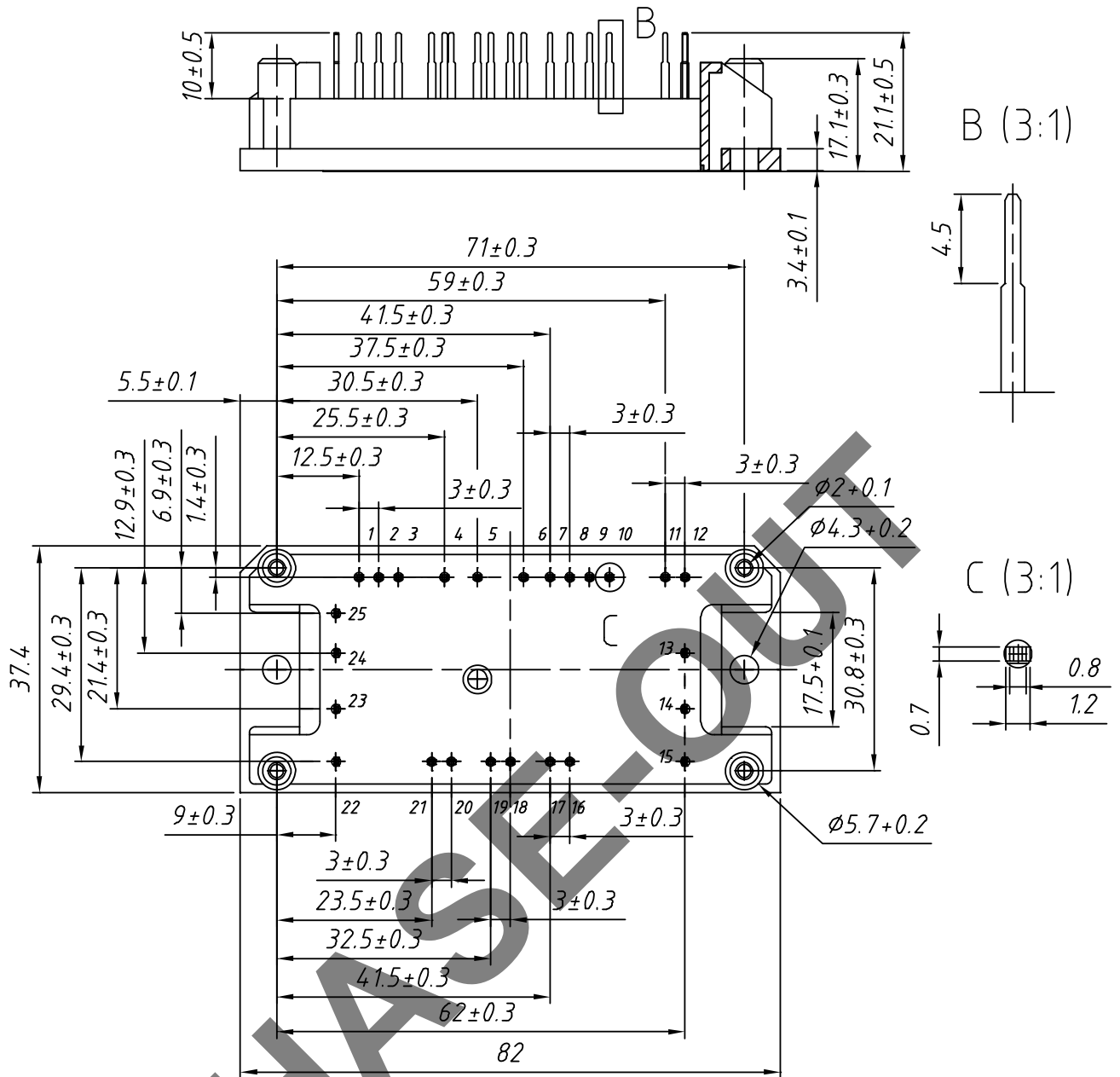
Equivalent Circuits for Simulation


Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_0	rectifier diode	D8 - D13	$T_{VJ} = 125^\circ\text{C}$	0.90		V
R_0				12		m Ω
V_0	IGBT	T1 - T6	$T_{VJ} = 125^\circ\text{C}$	1.4		V
R_0				150		m Ω
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^\circ\text{C}$	1.25		V
R_0				26		m Ω
V_0	IGBT	T7	$T_{VJ} = 125^\circ\text{C}$	1.4		V
R_0				150		m Ω
V_0	free wheeling diode	D7	$T_{VJ} = 125^\circ\text{C}$	1.25		V
R_0				26		m Ω

 $T_C = 25^\circ\text{C}$ unless otherwise stated

Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MUBW 10-06A6K	MUBW10-06A6K	Box	10	500 087

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Discrete Semiconductor Modules](#) category:

Click to view products by [IXYS](#) manufacturer:

Other Similar products are found below :

[M252511FV](#) [DD260N12K-A](#) [DD380N16A](#) [DD89N1600K-A](#) [APT2X21DC60J](#) [APT58M80J](#) [B522F-2-YEC](#) [MSTC90-16](#) [25.163.0653.1](#)
[25.163.2453.0](#) [25.163.4253.0](#) [25.190.2053.0](#) [25.194.3453.0](#) [25.320.4853.1](#) [25.320.5253.1](#) [25.326.3253.1](#) [25.326.3553.1](#) [25.330.1653.1](#)
[25.330.4753.1](#) [25.330.5253.1](#) [25.334.3253.1](#) [25.334.3353.1](#) [25.350.2053.0](#) [25.352.4753.1](#) [25.522.3253.0](#) [T483C](#) [T484C](#) [T485F](#) [T485H](#)
[T512F-YEB](#) [T513F](#) [T514F](#) [T554](#) [T612FSE](#) [25.161.3453.0](#) [25.179.2253.0](#) [25.194.3253.0](#) [25.325.1253.1](#) [25.326.4253.1](#) [25.330.0953.1](#)
[25.332.4353.1](#) [25.350.1653.0](#) [25.350.2453.0](#) [25.352.1453.0](#) [25.352.1653.0](#) [25.352.2453.0](#) [25.352.5453.1](#) [25.522.3353.0](#) [25.602.4053.0](#)
[25.640.5053.0](#)